



# SIGC12T120LE

## IGBT3 Power Chip

### Features:

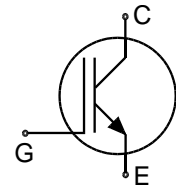
- 1200V Trench + Field Stop technology
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling

### This chip is used for:

- power module

### Applications:

- drives



Chip Type	V <sub>CE</sub>	I <sub>CN</sub>	Die Size	Package
SIGC12T120LE	1200V	8A	3.54 x 3.5 mm <sup>2</sup>	sawn on foil

### MECHANICAL PARAMETER

Raster size	3.54 x 3.5	mm <sup>2</sup>
Emitter pad size (incl. gate pad)	2.028 x 2.028	
Gate pad size	1.107 x 0.702	
Area total / active	12.39 / 6.82	
Thickness	120	µm
Wafer size	200	mm
Max.possible chips per wafer	2243 pcs	
Passivation frontside	Photoimide	
Pad metal	3200 nm AlSiCu	
Backside metal	Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	Electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject ink dot size	Ø 0.65mm ; max 1.2mm	
Recommended storage environment	Store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	



# SIGC12T120LE

## MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Collector-Emitter voltage, $T_j=25\text{ °C}$	$V_{CE}$	1200	V
DC collector current, limited by $T_{j\max}$	$I_C$	<sup>1)</sup>	A
Pulsed collector current, $t_p$ limited by $T_{j\max}$	$I_{C,puls}$	24	A
Gate emitter voltage	$V_{GE}$	$\pm 20$	V
Maximum junction and storage temperature	$T_{vj,max}$ , $T_{stg}$	-55 ... +150	°C
Short circuit data <sup>2)</sup> $V_{GE} = 15V$ , $V_{CC} = 900V$ , $T_{vj} = 125\text{ °C}$	$t_{p,max}$	10	$\mu s$
Reverse bias safe operating area <sup>2)</sup> (RBSOA)	$I_{C,max} = 16A$ , $V_{CE,max} = 1200V$ , $T_{vj,op} \leq 125\text{ °C}$		

<sup>1)</sup> depending on thermal properties of assembly

<sup>2)</sup> not subject to production test - verified by design/characterization

## STATIC CHARACTERISTICS (tested on wafer), $T_j=25\text{ °C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-Emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V$ , $I_C=0.5mA$	1200			V
Collector-Emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15V$ , $I_C=8A$	1.4	1.7	2.1	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$I_C=0.3mA$ , $V_{GE}=V_{CE}$	5.0	5.8	6.5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V$ , $V_{GE}=0V$			1.23	$\mu A$
Gate-Emitter leakage current	$I_{GES}$	$V_{CE}=0V$ , $V_{GE}=20V$			120	nA
Integrated gate resistor	$R_{Gint}$			none		$\Omega$

## ELECTRICAL CHARACTERISTICS (not subject to production test - verified by design / characterization)

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	$C_{iss}$	$V_{CE}=25V$ , $V_{GE}=0V$ , $f=1MHz$		600		pF
Output capacitance	$C_{oss}$			36		
Reverse transfer capacitance	$C_{rss}$			28		